STK1828EF

N-Channel Enhancement-Mode MOSFET

Description

- High speed switching application.
- Analog switch application.

Features

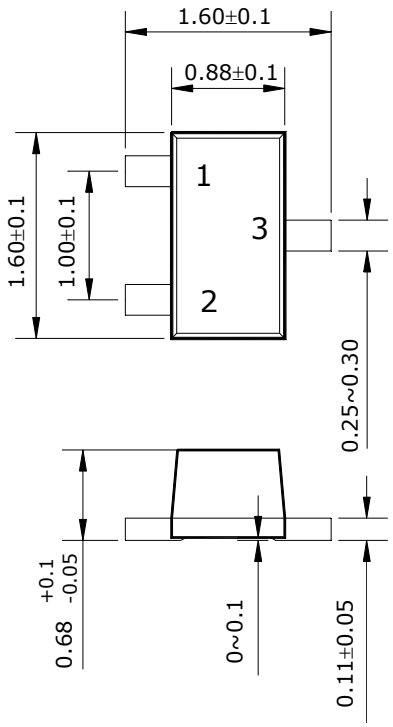
- 2.5V Gate drive.
- Low threshold voltage : Vth = 0.5~1.5V.
- High speed.

Ordering Information

Type NO.	Marking	Package Code
STK1828EF	K8	SOT-523F

Outline Dimensions

unit : mm



PIN Connections
1. Gate
2. Source
3. Drain

Absolute maximum ratings (Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Drain-Source voltage	V_{DS}	20	V
Gate-Source voltage	V_{GSS}	10	V
DC Drain current	I_D	50	mA
Drain Power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Electrical Characteristics (Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-Source breakdown voltage	BV_{DSS}	I_D=100μA, V_{GS}=0	20			V
Gate-Threshold voltage	V_{th}	I_D=0.1mA, V_{DS}=3V	0.5		1.5	V
Drain cut-off current	I_{DSS}	V_{DS}=20V, V_{GS}=0			1	μA
Gate leakage current	I_{GSS}	V_{GS}=10V, V_{DS}=0			1	μA
Drain-Source on-resistance	$R_{DS(ON)}$	V_{GS}=2.5V, I_D=10mA		10	20	Ω
Forward transfer admittance	$\lvert Y_{fs} \rvert$	V_{DS}=3V, I_D=10mA	20			mS
Input capacitance	C_{iss}	V_{DS}=3V, V_{GS}=0, f=1MHz		5.5		pF
Output capacitance	C_{oss}	V_{DS}=3V, V_{GS}=0, f=1MHz		6.5		pF
Reverse Transfer capacitance	C_{rss}	V_{DS}=3V, V_{GS}=0, f=1MHz		1.6		pF
Turn-on time	t_{ON}	V_{DD}=3V, I_D=10mA V_{GEN}=0~2.5V		0.14		μs
Turn-off time	t_{OFF}	V_{DD}=3V, I_D=10mA V_{GEN}=0~2.5V		0.14		μs

Electrical Characteristic Curves

Fig.1 I_D - V_{DS}

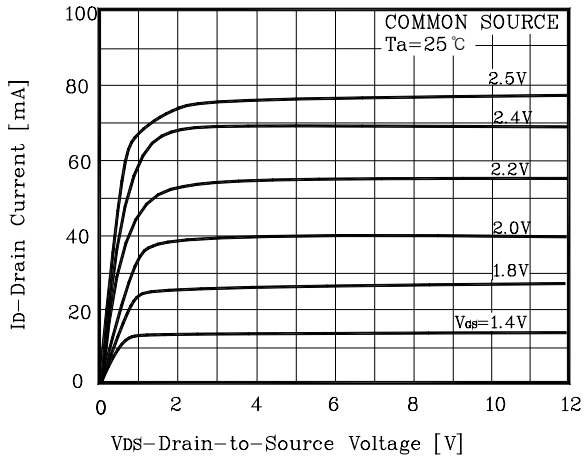


Fig.2 P_D - Ta

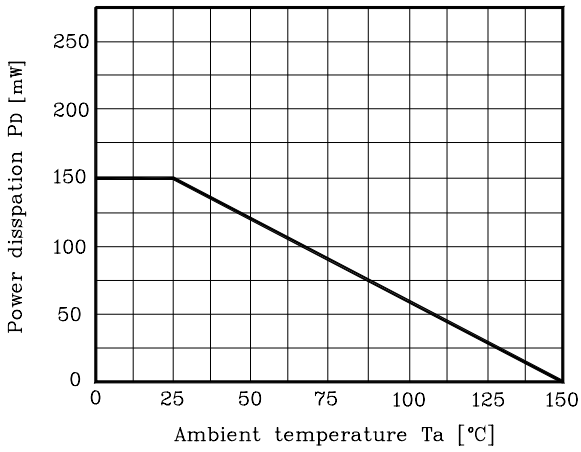


Fig.3 I_{DR} - V_{DS}

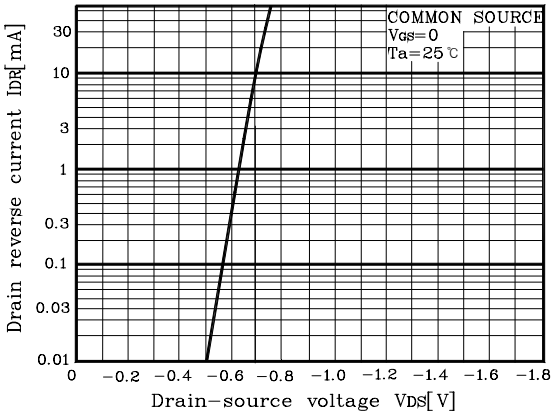


Fig.4 I_D - V_{GS}

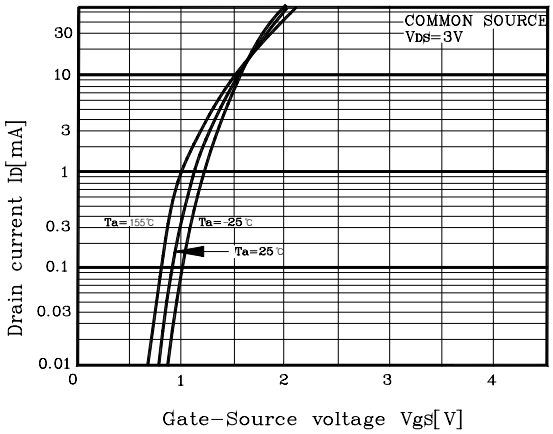


Fig.5 $|Y_{fs}|$ - I_D

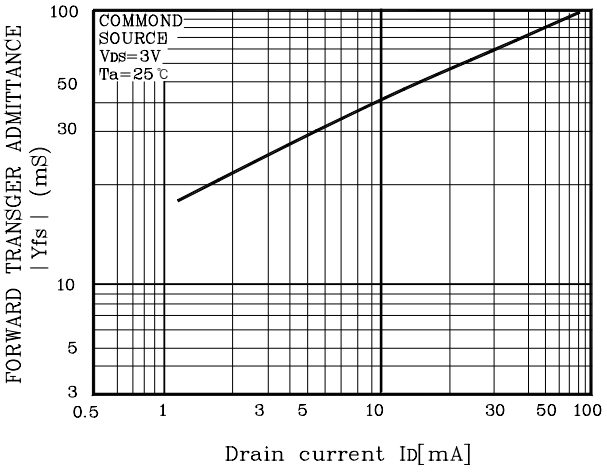
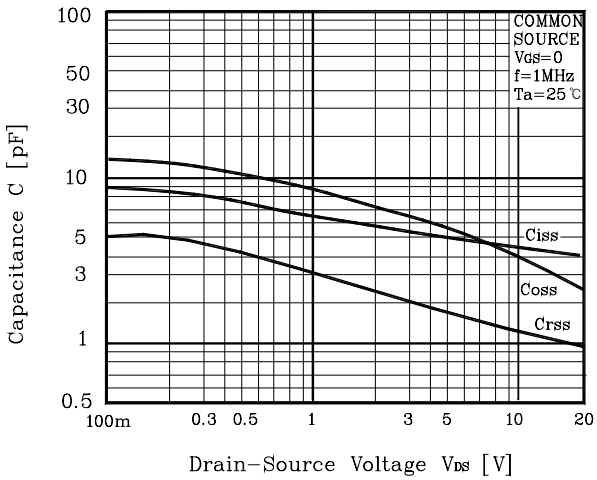


Fig.6 C - V_{DS}



Electrical Characteristic Curves

Fig.7 V_{DS} - I_D

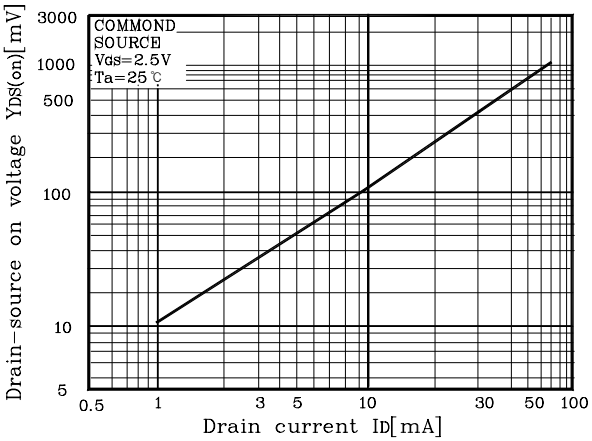


Fig.8 t - I_D